

ABSTRACT

A semiconductor device may include an element isolation film on a substrate, a first gate electrode, and an auxiliary electrode on the element isolation film. The element isolation film may define a first active area of the substrate. A first source/drain area and a second source/drain area of a first conductivity type may be in the first active area. The second source/drain area may be spaced apart from the first source/drain area in a first direction. The first gate electrode may be on a portion of the first active area between the first source/drain area and the second source/drain area. The first gate electrode may extend in a second direction crossing the first direction. The substrate may include an impurity area surrounding the element isolation film. The impurity area may contain a second conductivity type impurity. The auxiliary electrode and the impurity area may be electrically connected to each other.

FIG. 1